

## SPECIFICATION OF LED CHIP

C1050-45

[NIR]

### 1) Commodity Type and Physical Characteristics.

- |                      |                   |                  |            |
|----------------------|-------------------|------------------|------------|
| 1. Material          | InGaAsP/GaAs(DDH) |                  |            |
| 2. Electrode         | Top Side          | P (anode) side   | : Au Alloy |
|                      | Bottom Side       | N (cathode) side | : Au Alloy |
| 3. Electrode Pattern | Fig.1             |                  |            |
| 4. Chip Size         | Fig.2             |                  |            |
| 5. Chip Thickness    | Fig.2             |                  |            |
| 6. Emission Area     | Fig.2             |                  |            |

### 2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.00	1.15	V
		If=100mA		1.25	1.35	
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA		0.8		mW
Peak Wavelength	$\lambda_P$	If=20mA	1030	1050	1080	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		80		nm
RiseTime	tr	If=20mA		20		ns
FallTime	tf	If=20mA		20		ns

‡ Die shall be mounted on TO=18 gold header without resin coated. (Ta=25°C)

[Unit: um]

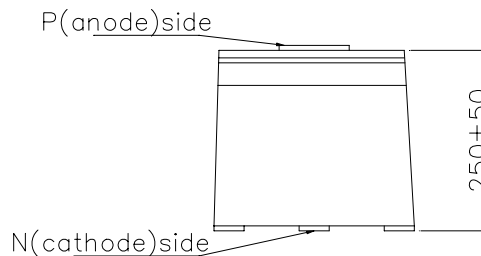
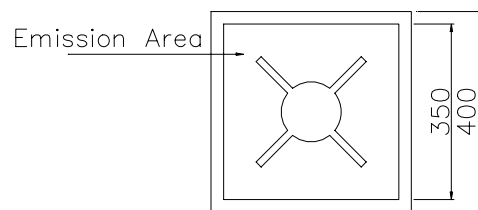
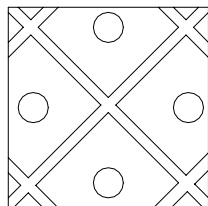
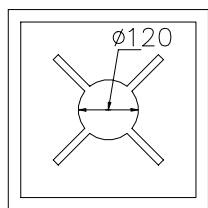


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area

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